ALPHA & OMEGA SEMICONDUCTOR

AONV240V70GA1

700V GaN Enhancement-mode Power Transistor

Features

- 700V GaN enhancement-mode transistor
- Normally-off design
- No Qrr (reverse recovery charge)
- Low Qg (gate charge), low Qoss (output charge)
- Integrated ESD protection

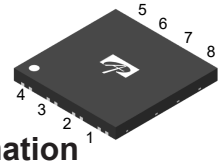
Applications

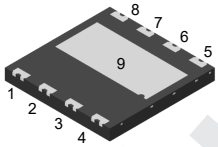
- AC/DC and DC/DC converters, totem pole PFC, fast battery charging, high density and high efficiency power conversion

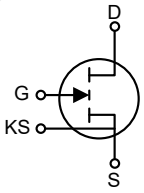
Product Summary at T_J = 25°C

$V_{DS, max}$	700V
$R_{DS(on), max}$ @ V_{GS} = 6V	240mΩ
$Q_{g, typ}$ @ V_{DS} = 400V	2nC
$I_{D, pulse}$	18A
Q_{oss} @ V_{DS} = 400V	21nC
Q_{rr} @ V_{DS} = 400V	0nC

Pin Configuration







Pin Information

Gate	Drain	Kelvin Source	Source
8	1, 2, 3, 4	7	5, 6, 9

Ordering Information

Ordering Part Number	Package Type	Form	Shipping Quantity
AONV240V70GA1	DFN8x8	Tape and Reel	1500

Contact local sales office for full product datasheet.

Absolute Maximum Ratings

(T_J = 25°C, unless otherwise noted)

Symbol	Parameter		AONV240V70GA1	Units
$V_{DS, max}$	Drain Source Voltage	V_{GS} = 0V, T_J = -55°C to 150°C	700	V
$V_{DS, trans}$	Drain Source Voltage Transient (1)	V_{GS} = 0V	800	
$V_{DS, pulse}$	Drain Source Voltage Pulsed (2)	T_C = 25°C, total time < 10 hours	750	
		T_C = 125°C, total time < 1 hour		
I_D	Continuous Drain Current	T_C = 25°C	10	A
$I_{D, pulse}$	Pulsed Drain Current (3)	T_C = 25°C, V_{GS} = 6V, t_{pulse} = 10µs	18	
		T_C = 125°C, V_{GS} = 6V, t_{pulse} = 10µs	10	
V_{GS}	Gate Source Voltage, Continuous (4)	T_J = -55°C to 150°C	-6 to 7	V
$V_{GS, pulse}$	Gate Source Voltage, Pulsed	T_J = -55°C to 150°C, t_{pulse} = 50ns, f = 100kHz, open drain	-20 to 10	V
P_{tot}	Power Dissipation (5)	T_C = 25°C	76	W
$T_{j, stg}$	Operating and Storage Temperature		-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ	Max	Note	Units
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient (6)	66			°C/W
$R_{\theta JC}$	Thermal Resistance Junction-to-Case	1.64			°C/W
T_{sold}	Maximum Reflow Soldering Temperature	260		MSL3	°C

Electrical Characteristics

(T_J = 25°C, unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
STATIC PARAMETERS							
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} , I_D = 11mA	T_J = 25°C	1.2	1.7	2.5	V
			T_J = 150°C		1.7		
I_{DSS}	Drain-Source Leakage Current	V_{DS} = 700V, V_{GS} = 0V	T_J = 25°C		0.4	20	µA
			T_J = 150°C		5		
I_{GSS}	Gate-Source Leakage Current	V_{GS} = 6V, V_{DS} = 0V			50		µA
$R_{DS(on)}$	Drain-Source On-State-Resistance	V_{GS} = 6V, I_D = 3A	T_J = 25°C		165	240	mΩ
			T_J = 150°C		360		
R_G	Gate Resistance	f = 5 MHz; open drain			6		Ω
DYNAMIC							
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 400V, f = 100kHz			79		pF
C_{oss}	Output Capacitance				25		
C_{rss}	Reverse Transfer Capacitance				0.2		
$C_{o(er)}$	Effective Output Capacitance Energy Related (7)	V_{GS} = 0V, V_{DS} = 0 to 400V			36		pF
$C_{o(tr)}$	Effective Output Capacitance Time Related (8)				52		
Q_{oss}	Output Charge				21		nC
$t_{d(on)}$	Turn-On Delay Time	V_{DS} = 400V, I_D = 6A, L = 318µH, V_{GS} = 6V, R_{on} = 10Ω, R_{off} = 2Ω, See Figure 22			2		ns
$t_{d(off)}$	Turn-Off Delay Time				4		
t_r	Rise Time				5		
t_f	Fall Time				6		
GATE CHARGE							
Q_G	Gate Charge	V_{GS} = 0 to 6V, V_{DS} = 400V, I_D = 3A			2		nC
Q_{GS}	Gate Source Charge				0.2		
Q_{GD}	Gate Drain Charge				0.7		
V_{Plat}	Gate Plateau Voltage	V_{DS} = 400V, I_D = 3A			2.5		V

Electrical Characteristics *(Continued)*

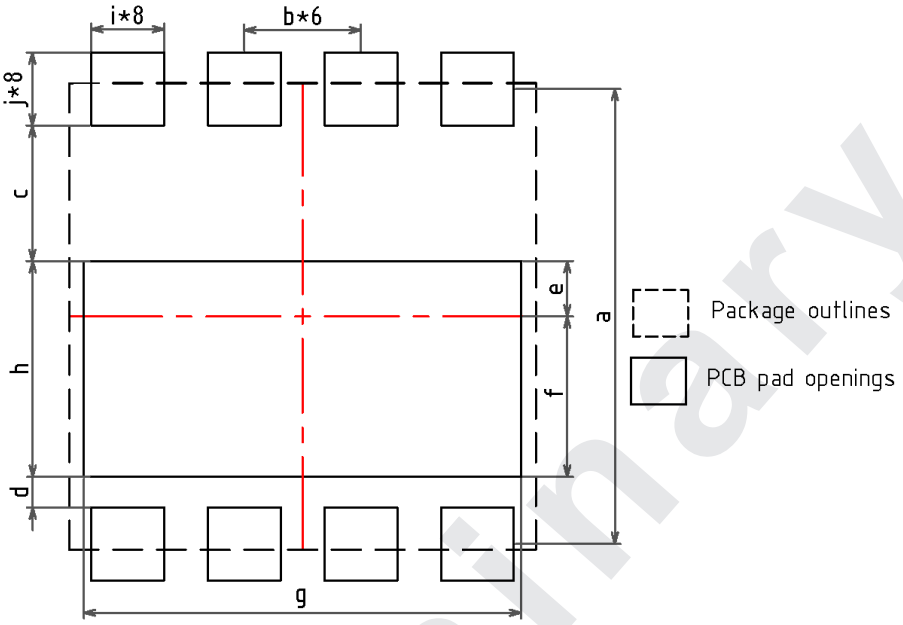
(T_J = 25°C, unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
REVERSE CONDUCTION							
V_{SD}	Source-Drain Reverse Voltage	V_{GS} = 0V, I_S = 3A			2.6		V
$I_{S, pulse}$	Reverse Pulsed Current	V_{GS} = 6V, t_{pulse} = 10µs				18	A
Q_{rr}	Reverse Recovery Charge	I_S = 3A, V_{DS} = 400V			0		nC
t_{rr}	Reverse Recovery Time				0		ns
I_{rrm}	Peak Reverse Recovery Current				0		A

Notes:

1. $V_{DS,transient}$ is intended for non-repetitive events, t_{PULSE} < 200µs.
2. $V_{DS,pulse}$ is intended for repetitive pulse, t_{PULSE} < 100ns.
3. Limit was extracted from characterization test, not measured during production.
4. The minimum V_{GS} is clamped by ESD protection circuit, as shown in Figure 8.
5. Power dissipation, and consequently max. current ratings are obtained using max. thermal resistance and max. temperature of 150°C.
6. $R_{\theta JA}$ is determined with the device mounted on one square inch of copper pad, single layer 2oz copper on FR4 board.
7. $C_{o(er)}$ is the fixed capacitance that gives the same stored energy as C_{oss} while VDS is rising from 0 to 400V.
8. $C_{o(tr)}$ is the fixed capacitance that gives the same charging time as C_{oss} while VDS is rising from 0 to 400V.

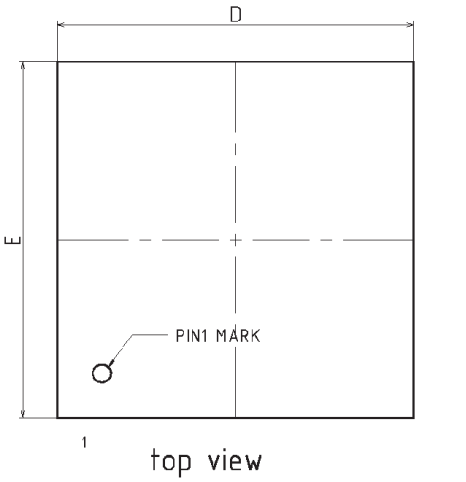
Recommended PCB Footprint

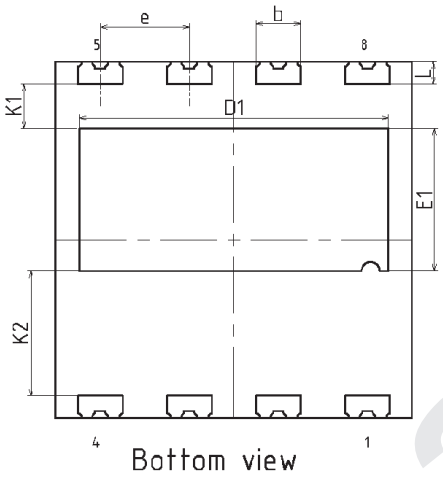


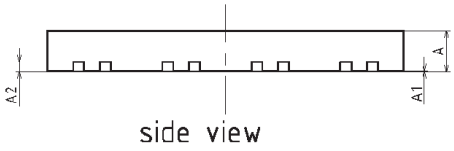
SYMBOL	DIMENSION	SYMBOL	DIMENSION
a	7.800	f	2.750
b	2.000	g	7.500
c	2.325	h	3.700
d	0.525	i	1.400
e	0.950	j	1.250

Notes:
(1)All dimension are in millimeters.
(2)Drawing is not to scale.

Package Dimensions, DFN8x8





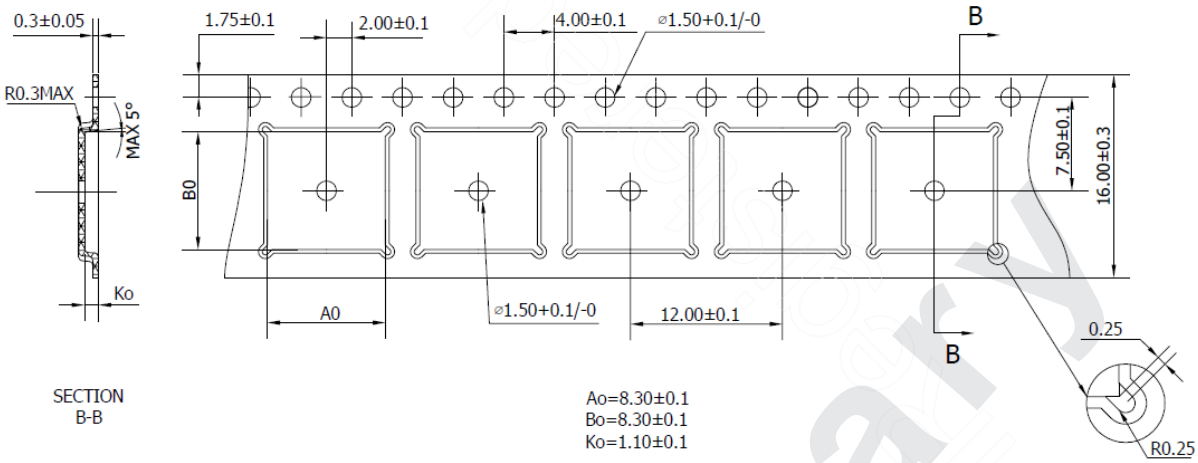


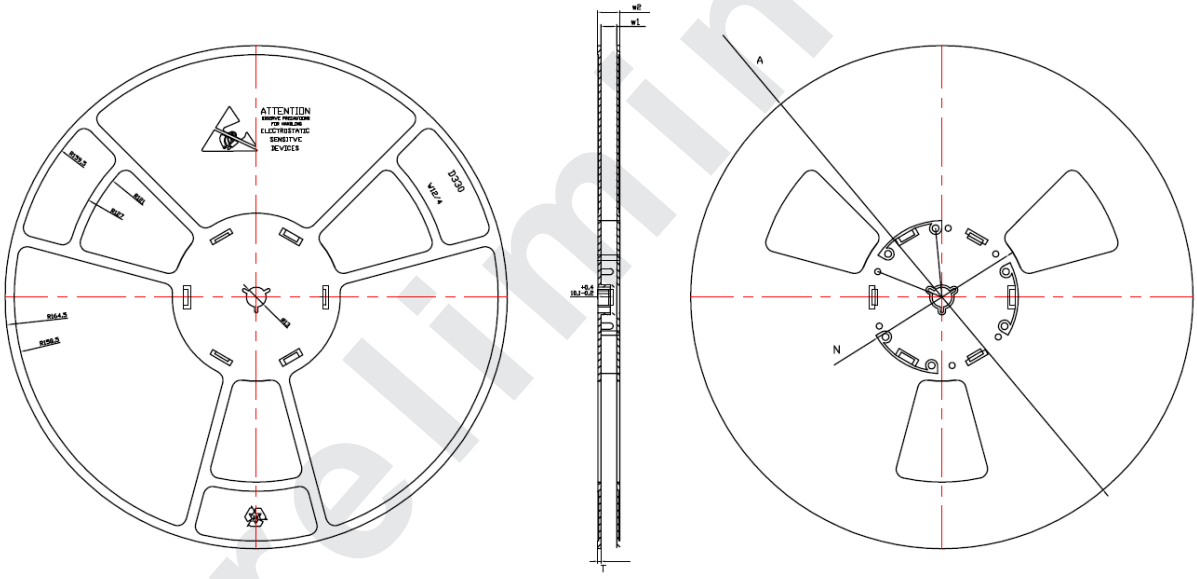
SYMBOL	DIMENSION		
	MIN	NOM	MAX
A	0.80	0.90	1.00
A1	0.00	0.02	0.05
A2		0.203REF	
b	0.95	1.00	1.05
D		8.00 BSC	
D1	6.84	6.94	7.04
E		8.00 BSC	
E1	3.10	3.20	3.30
K1	0.90	1.00	1.10
K2	2.70	2.80	2.90
e		2.00 BSC	
L	0.40	0.50	0.60

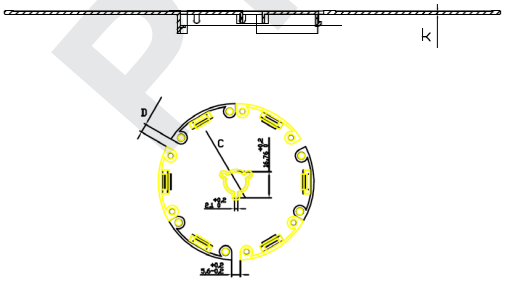
Notes:

1. Dimension and tolerance conform to ASME Y14.5-2009.
2. All dimensions are in millimeters.
3. Lead coplanarity will be 0.1 millimeters max.
4. Complies with JEDEC MO-229.
5. Drawing is not to scale.
6. Dimensions do not include mold protrusion.
7. Package outline exclusive of metal burr dimensions.

Tape and Reel Dimensions, DFN8x8







SYMBOL	DIMENSION(mm)		
	MIN	NOM	MAX
A	328	330	332
N	98	100	102
C	12.90	13.10	13.30
D	5.10	5.60	6.10
w1	16.40	16.40	18.40
w2	20.60	20.60	22.60
T	1.95	2.10	2.25
K	1.30	1.40	1.55

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